

MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT

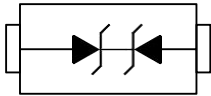


PLED

Product data sheet



SOD-923



Feature

- 80W peak pulse power per line ($t_P = 8/20\mu s$)
- SOD-923 package
- Replacement for MLV(0402)
- Bidirectional configurations
- Response time is typically $< 1ns$
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to
EC61000-4-2(ESD) $\pm 30KV$ (air), $\pm 30KV$ (contact);
IEC61000-4-4 (EFT) 40A (5/50ns)

Applications

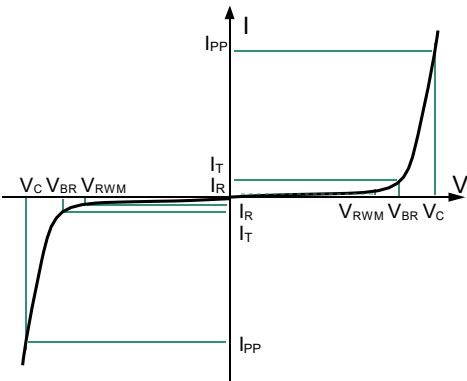
- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

Mechanical Characteristics

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260℃
- Device meets MSL 1 requirements
- Pure tin plating: 7 ~ 17 um
- Pin flatness: $\leq 3mil$

Electronics Parameter

Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
P_{PP}	Peak Pulse Power
C_J	Junction Capacitance
I_F	Forward Current
V_F	Forward Voltage @ I_F

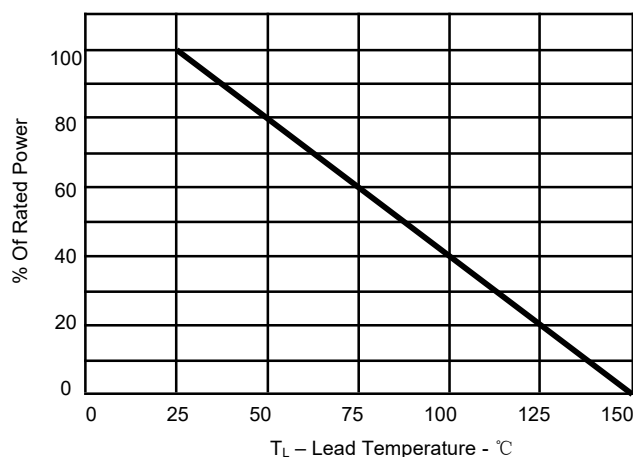
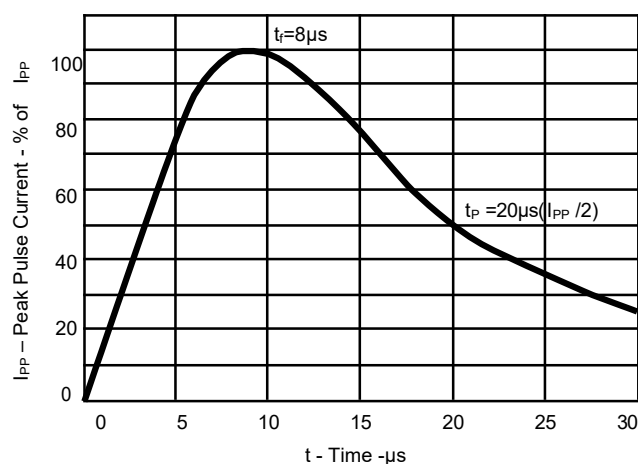


Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Peak Reverse Working Voltage	V_{RWM}				5	V
Breakdown Voltage	V_{BR}	$I_t = 1mA$	5.6	6.7	7.8	V
Reverse Leakage Current	I_R	$V_{RWM} = 5V$ $T=25^{\circ}C$			1.0	μA
Maximum Reverse Peak Pulse Current	I_{PP}			5		A
Clamping Voltage	V_C	$I_{PP}=1A$			8	V
Clamping Voltage	V_C	$I_{PP}=3A$			13	V
Clamping Voltage	V_C	$I_{PP}=5A$			15	V
Junction Capacitance	C_j	$V_R=0V$ $f = 1MHz$		12	15	pF

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Peak Pulse Power ($t_p=8/20\mu s$)	P_{pp}	80	W
Operating Temperature	T_J	-55 to +150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 to +150	$^{\circ}C$

Typical Characteristics


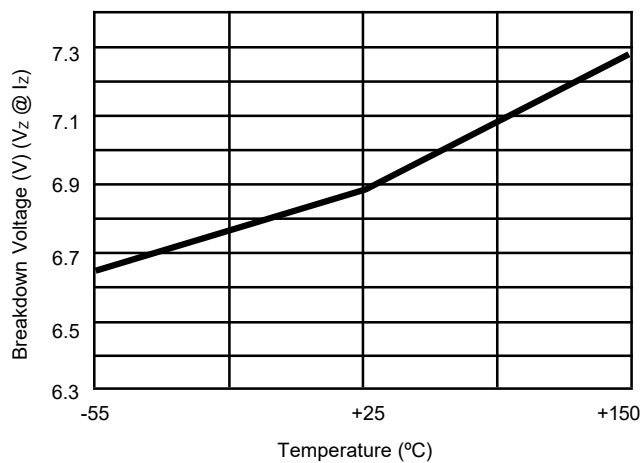


Fig 3. Typical Breakdown Voltage vs. Temperature

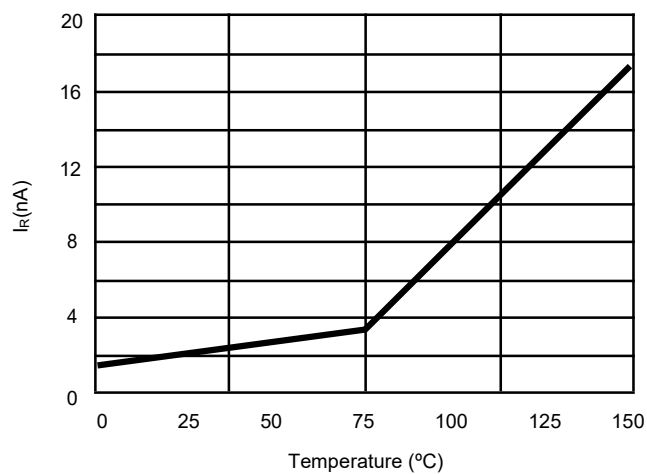


Fig 4. Typical Leakage Current vs. Temperature

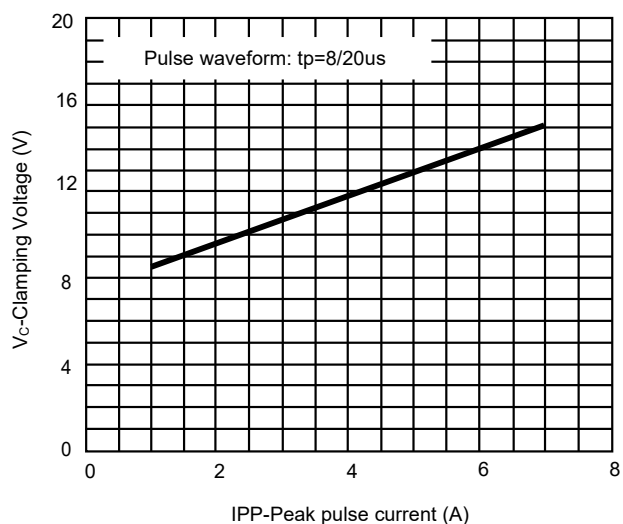


Fig 5. Clamping voltage vs. Peak pulse current

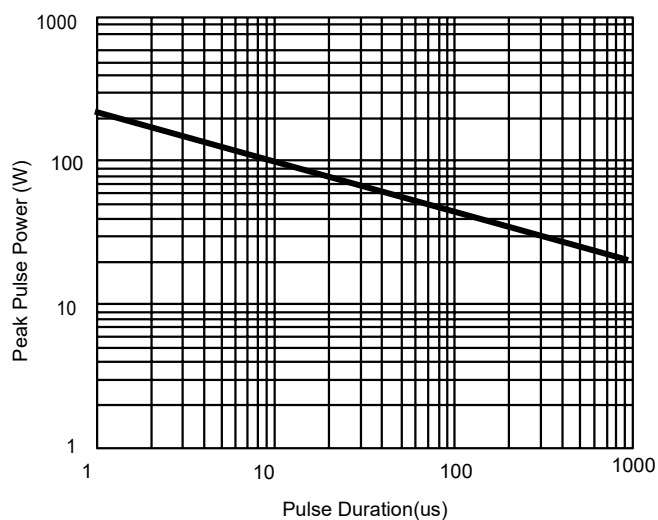
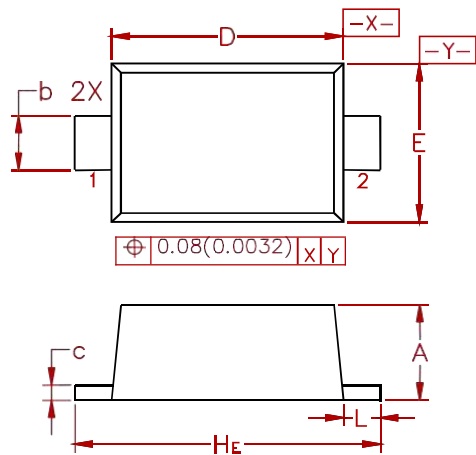


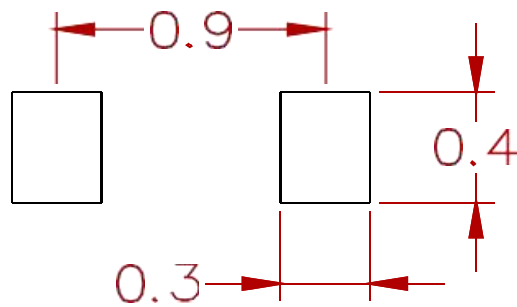
Fig 6. Non-Repetitive Peak Pulse Power vs. Pulse time

PACKAGE MECHANICAL DATA



Dim	Millimeters			Inches		
	Min	Nom	Max	Min	Nom	Max
A	0.36	0.40	0.43	0.014	0.016	0.017
b	0.15	0.20	0.25	0.006	0.008	0.010
c	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	0.95	1.00	1.05	0.037	0.039	0.041
L	0.05	0.10	0.15	0.002	0.004	0.006

Suggested Pad Layout



Dimensions: Millimeters

REEL SPECIFICATION

P/N	PKG	QTY
ESD9X5.0ST5G	SOD-923	8000

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